

ABSTRACT OF THE DISCLOSURE

A method for the production of a silicon single crystal by pulling the single crystal, according to the Czochralski method, from a melt which is held in a rotating crucible, the single crystal growing at a growth front, heat being deliberately supplied to the center of the growth front by a heat flux directed at the growth front. The method produces a silicon single crystal with an oxygen content of from $4 \times 10^{17} \text{ cm}^{-3}$ to $7.2 \times 10^{17} \text{ cm}^{-3}$ and a radial concentration change for boron or phosphorus of less than 5%, which has no agglomerated self-point defects. Semiconductor wafers are separated from the single crystal. These semiconductor wafers have may have agglomerated vacancy defects (COPs) as the only self-point defect type or may have certain other defect distributions.